

Features

- · Split Gate Trench MOSFET Technology
- · Low Thermal Resistance
- Halogen Free. "Green" Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

Maximum Ratings

Operating Junction Temperature Range : -55°C to +150°C

Storage Temperature Range: -55°C to +150°C

Thermal Resistance: 40°C/W Junction to Ambient (Note2)

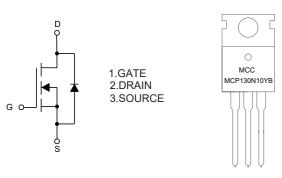
• Thermal Resistance: 0.5°C/W Junction to Case

Parameter		Symbol	Rating	Unit	
Drain-Source Voltage		V _{DS}	100	V	
Gate-Source Volltage		V _{GS}	±20	V	
Continuous Drain Current	T _C =25°C		130	Α	
	T _C =100°C	– I _D	82		
Pulsed Drain Current (Note 3)		I _{DM}	520	Α	
Total Power Dissipation ^(Note4)		P _D	250	W	
Avalanche Energy (Note 5)		E _{AS}	AS 340		

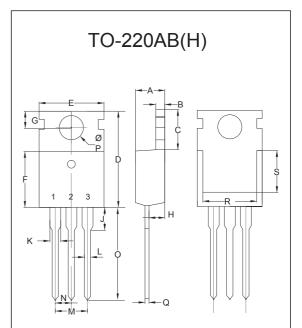
Note:

- 1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 2. The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C.
- ${\it 3. Repetitive\ rating; pulse\ width\ limited\ by\ max.\ junction\ temperature.}$
- 4. P_D is based on max. junction temperature, using junction-case thermal resistance.
- 5. T_J =25°C, V_{DD} =50V, V_{GS} =10V, R_G =25 Ω , L=0.5mH.

Internal Structure and Marking Code



N-Channel Enhancement Mode Field Effect Transistor



	INCI MIN .172	HES MAX	MIN	M	NOTE	
		MAX	NAINI		NOTE	
A 0	.172		IVIIIN	MAX	NOTE	
		0.188	4.37	4.77		
B 0	.049	0.057	1.25	1.45		
C 0	.246	0.270	6.25	6.85		
D 0	.594	0.634	15.10	16.10		
E 0	.382	0.406	9.70	10.30		
F 0	.346	0.370	8.80	9.40		
G 0	.102	0.118	2.60	3.00		
H 0	.087	0.102	2.20	2.60		
J		0.134		3.40		
K 0	.046	0.058	1.17	1.47		
L 0	.028	0.037	0.70	0.95		
М	0.200		5.08		TYP.	
N	0.1	00	2.	54	TYP.	
0 0	.502	0.543	12.75	13.80		
P 0	.134	0.150	3.40	3.80	Ф	
Q 0	.016	0.026	0.40	0.65		
R 0	.276		7.00			
S 0	.217		5.50			

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Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static Characteristics				1	1		
Drain-Source Breakdown Voltage	BV _{(BR)DSS}	V _{GS} =0V, I _D =250μA	100			V	
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V			±100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V			1	μΑ	
		V _{DS} =100V, V _{GS} =0V,Tj=150°C			100		
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1	1.8	2.5	٧	
Drain-Source On-Resistance		V _{GS} =10V, I _D =65A		4	5.5	mΩ	
	R _{DS(on)}	V _{GS} =4.5V, I _D =20A		5	6.5		
Continuous Body Diode Current	R _G	f=1MHZ,Open drain		0.8		Ω	
Diode Characteristics							
Diode Forward Current	Is				130	Α	
Gate resistance	V _{SD}	V _{GS} =0V, I _S =65A		0.9	1.2	٧	
Reverse Recovery Time	t _{rr}	I _F =65A,di/dt=700A/μs		37		ns	
Reverse Recovery Charge	Q _{rr}	1		170		nC	
Dynamic Characteristics							
Input Capacitance	C _{iss}			4350			
Output Capacitance	C _{oss}	V _{DS} =50V,V _{GS} =0V,f=100KHz		1780		pF	
Reverse Transfer Capacitance	C _{rss}			28			
Total Gate Charge	Qg			69			
Gate-Source Charge	Q _{gs}	V _{DS} =50V,V _{GS} =10V,I _D =65A		14		nC	
Gate-Drain Charge	Q_{gd}			13			
Turn-On Delay Time	t _{d(on)}			14			
Turn-On Rise Time	t _r	V _{DD} =50V,V _{GS} =10V,		90		- ns	
Turn-Off Delay Time	t _{d(off)}	$R_G=2.2\Omega$ $I_D=65A$		42			
Turn-Off Fall Time	t _f			12			



Curve Characteristics

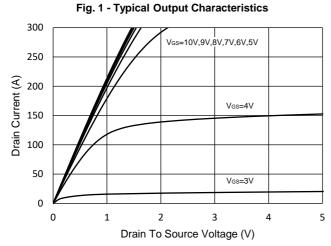


Fig.2 - Transfer Characteristic

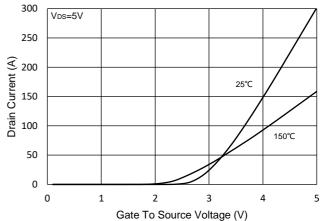


Fig.3 - R_{DS(ON)} - V_{GS}

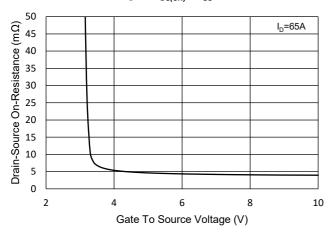


Fig.4 - $R_{DS(ON)}$ - I_D

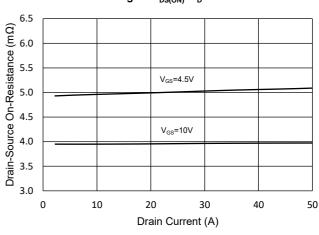


Fig.5 - Capacitance Characteristics

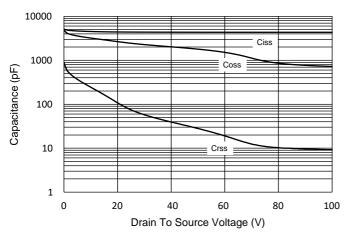
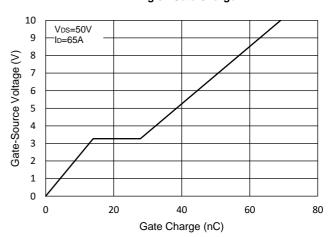
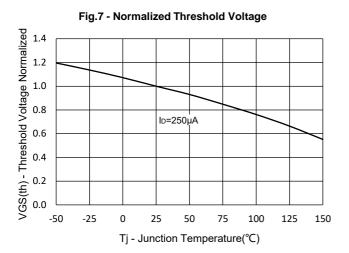


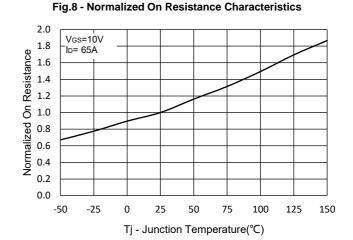
Fig.6 - Gate Charge

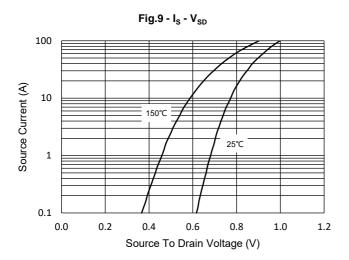


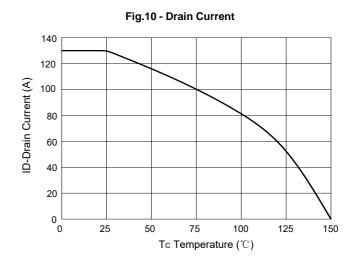


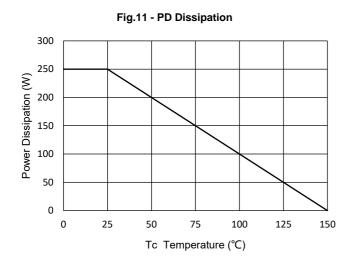
Curve Characteristics





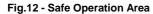








Curve Characteristics



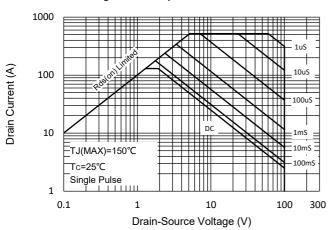
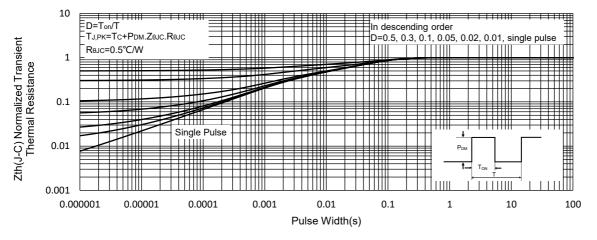


Fig.13 - Normalized Transient Thermal Impedance





Ordering Information

Device	Packing		
Part Number-BP	Bulk:50pcs/Tube,1Kpcs/Box,5Kpcs/Carton		

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